Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low forward voltage drop
- Low thermal resistance
- · Soft recovery characteristic
- · Enhanced avalanche energy capability

3. Applications

- · High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit			
Absolute maximum rating									
V_{RRM}	repetitive peak reverse voltage		600				V		
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_h \le 71$ °C; Fig. 1; Fig. 2; Fig. 3			10		А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 71 °C; square-wave pulse		:	20		А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	75		А				
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	83			Α			
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit			
Static ch	aracteristics								
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.55	2	V		
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	-	1.6	V		
Dynamic	characteristics								
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	35	50	ns		
		$I_F = 10 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	50	-	ns		
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	78	-	ns		
		$I_F = 10 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	42	-	ns		

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated		

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BYV10EX-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113				

7. Marking

Table 4. Marking codes

- auto- it illustrating course	
Type number	Marking codes
BYV10EX-600P	BYV10EX-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; $T_h \le 71$ °C; Fig. 1; Fig. 2; Fig. 3	10	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 71 °C$; square-wave pulse	20	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	75	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	83	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

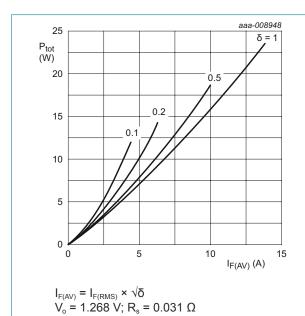
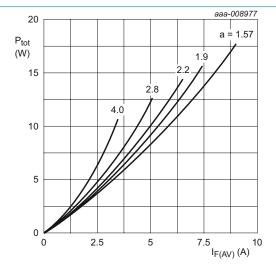
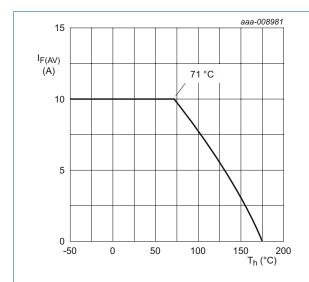


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 1.268 V; Rs = 0.031 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values





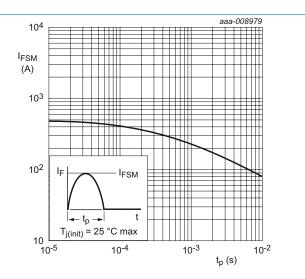
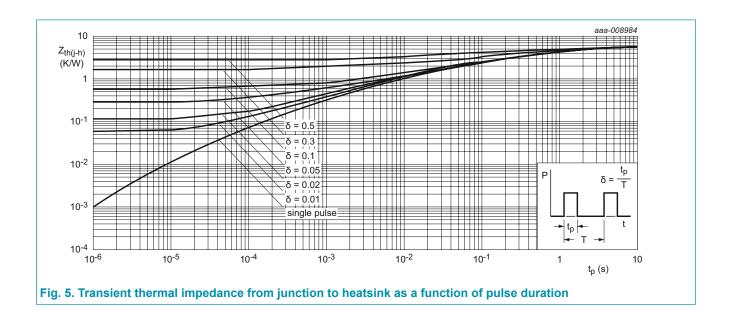


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	With heatsink compound; Fig. 5	-	-	5.5	K/W
	heatsink	Without heatsink compound	-	-	7.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

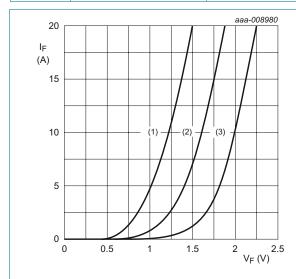
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	PF

11. Characteristics

Table 7. Characteristics

<u> </u>	Taracteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
V_{F}	forward current	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	1.55	2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	-	1.6	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	-	10	μA
		V _R = 600 V; T _j = 150 °C		-	-	250	μA
Dynamic	characteristics						
Q _r reverse ch	reverse charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	123	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	305	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	35	50	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	50	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	78	-	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	42	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_j = 25 ^{\circ}\text{C}$; Fig. 7	-	-	4.9	-	А
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	7.8	-	А
E _{as}	non-repetitive avalanche energy	I _R = 1.2 A; T _{j(init)} = 25 °C; L = 15 mH	1	8.01	-	-	mJ
	-	·					



 V_o = 1.268 V; R_s = 0.031 Ω

(1) $T_j = 150 \,^{\circ}\text{C}$; typical values (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values (3) $T_j = 25 \,^{\circ}\text{C}$; maximum values

Fig. 6. Forward current as a function of forward voltage

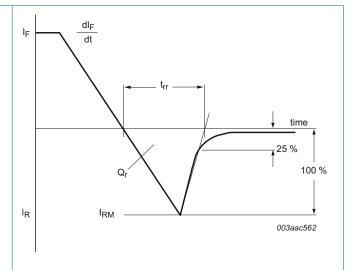


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline

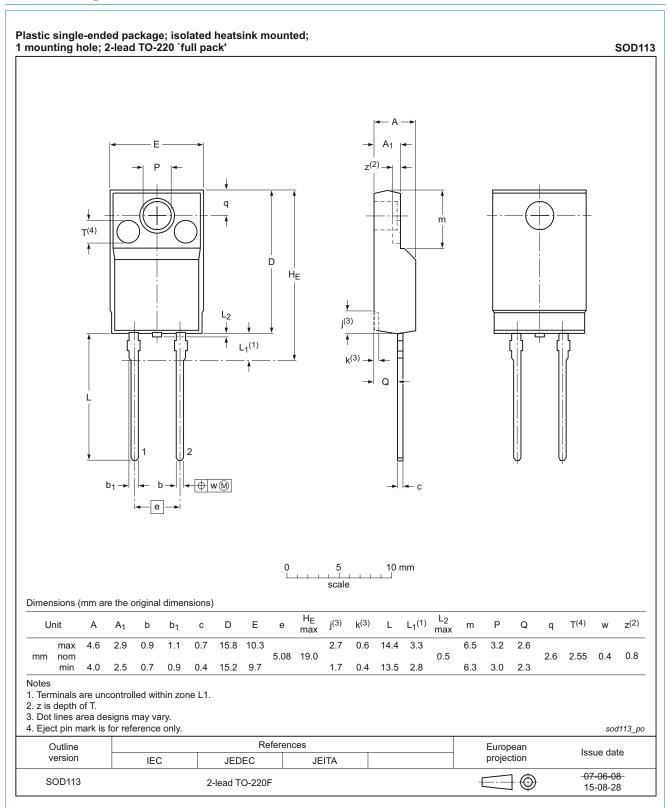


Fig. 8. Package outline SOD113 (TO-220F)

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BYV10EX-600P

Ultrafast power diode

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